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Kalman Filter for Indirect Measurement of Electrolytic Bath State Variables: *Tuning Design and Practical Aspects*

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Abstract: The development *Kalman* filter tuning model based on *QR* duality principle of the gain is the main issue of this article. The filter design is oriented to measure the most important state variable of the electrolytic bath, the percentual of alumina. The technical solution encloses on line evaluation of the *Kalman* filter working with a real production pot. The main goal is to compute a set of filter gains that represents the behavior of the alumina inside the cell. The design and analysis of the *Q* and *R* covariances matrices are exercised in order to find a pattern of the reduction cell resistance variations that may be associated with the Al_2O_3 concentration. The filter bandwidth tuning is performed by increasing or decreasing the filter bandpass from the *Q* and *R* variations. This research goes in the direction of practical aspects limits of the indirect measurement system implementations. The robustness of the filter is evaluated in terms of observability, roundoff and modeling errors. Copyright © 2008 IFSA.

Keywords: *Kalman* Filter Tuning, Reduction, Indirect Measurement, Electrolytic Bath and *QR* duality principle

1. Introduction

In this paper are presented some results of a research directed to the development of an alumina concentration indirect measurement system, [1]. The procedure to evaluate the best gain is based on *QR* covariance matrices duality principle, [2] and indirect measurement algorithm was coded in application software considering the computing restrictions of a real-time control system. The main idea stands to present the *Kalman* filter skills in pattern recognition of Al_2O_3 concentration, considering a strong interaction between Al_2O_3 and reduction cell electrical resistance variations.

The proposed problem solution is focused on the design of the digital *Kalman* filter gains to indirect measurement of electrolytic bath state variables. The filtered and predicted states are used to estimate the alumina concentration in the electrolytic bath, [9]. The standard formulations of the *Kalman* filter are discussed in [3] and [4]. The *Kalman* filter theory is strongly dependent on the plant model. Consequently, the identification of suitable model to represent the plant is essential to predict the states of the smelter pot.

The correlated research used to develop methods to adjust gains based on the noise covariances matrices are reported by [5]. A specific method, called the QR duality principle, [2], is incorporated in the QR estimation methods, [5] and [6], to improve the process model. Evolutionary computation methods have been applied to evaluate the best QR matrices selections, [7].

The paper is organized in Sections and one Appendix to describe the tuning method and its results to obtain the alumina indirect measurement. In Section 2 is presented the characterization of indirect measurement system designed to evaluate the Al_2O_3 in the electrolytic bath, the system basic components are the reduction cell model, the state space observers based on *Kalman* Filter and the measurements of current and voltage. The QR dual mathematical approximation for *Kalman* filter tuning and a general procedure for its bandwidth tuning are discussed in Section 3. The procedure for QR duality principle gains design of the SKF is presented in Section 4, tuning issues such as state space pot model stability and observability are computed. In section 5 the real time implementation of the gain adjustment is implemented in process computer and its results are evaluated to show flexibility of the *Kalman* filter theory, when is applied in the stochastic state space observers gain computation. The concluding remarks are pointed out in Section 6, the results are related to the *Kalman* filter evaluation of the proposed methodology that is oriented to indirect measurement.

2. Indirect Measurement System

The reduction cell model, state observers, standard *Kalman* filtering (SKF) theory and direct measurements devices are the scientific and technical basis of the proposed indirect measurement system. The diagram of Fig. 1 represents the proposed system of the plant and state observer, the SKF theory is used for tuning the state observer gains and the devices (sensors and current transformers) are used to measure the reduction cell voltages and currents.

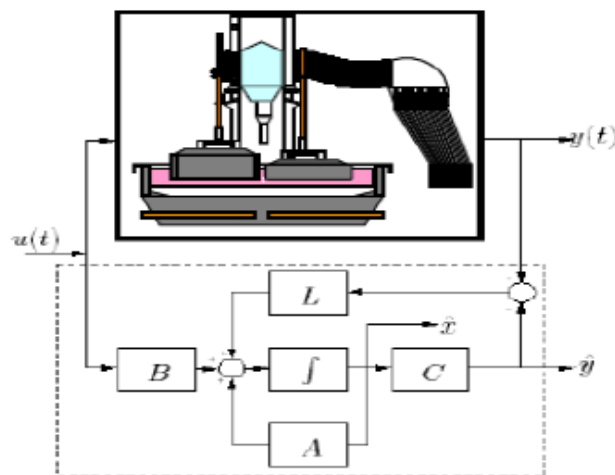


Fig. 1. The Reduction Cell and State Observer Block Diagram.

2.1. Reduction Cell Model

The reduction cell behavior model is a third order discrete linear stochastic system described, in the state variables by,

$$x_{k+1} = Ax_k + \Gamma v_k \quad (1)$$

$$y_k = Cx_k + w_k, \quad (2)$$

where $x_k \in \mathcal{R}^n$ represents the resistance, slope and curvature. The $y_k \in \mathcal{R}^n$ output represents the measured signal. $A \in \mathcal{R}^{n \times n}$ represents the system dynamics, $\Gamma \in \mathcal{R}^{n \times n}$ is the related noise input. $v_k \in \mathcal{R}^n$ and $w_k \in \mathcal{R}^n$ are the zero mean Gaussian white noise sequences with the known variances Q and R , respectively.

2.2. State Observers

The state observer main idea is the replacement of conventional measurements systems by a device based on hardware and software. The observer designed has two main issues that are the reduction cell model identification and gain adjustment. In a large sight, the state observers appliance is related with existence of noisy measurements, hard access and high cost of sensors. As seen in Fig. 1, the observers inputs are the measured output and control signals. The observer dynamic is given by,

$$\hat{x} = A\hat{x} + Bu + L_{estim}(y - C\hat{x}), \quad (3)$$

where L_{estim} is the observer gains that can be computed by deterministic or stochastic methods. In our case, the gains are computed by the *Kalman* filter theory and our system is driven by noise.

2.3. Direct Measurements

The reduction cell direct measurements are performed by the hardware devices, sensors of voltage and current connected to reduction cell. The sensors output signals are digitalized and processed in the process computer. For practical purposes, the measured output signals are associated with Eq. (2), y_k is the k^{th} output signal that can be represented by the state vector trajectory, Cx_k , and its noise signal, w_k .

2.4. Standard Kalman Filtering

A linear, unbiased and minimum error variance estimation of the reduction cell states, x_k , at instants k , is obtained by the SKF basic equations, [8] that assembles a recursive scheme given by

$$P^P = AP^F A^T + \Gamma Q \Gamma^T \quad (4)$$

$$x^P_{k+1} = Ax^P_k \quad (5)$$

$$K_K = P^P C^T + (C P^P C^T + R)^{-1} \quad (6)$$

$$x^F_{k+1} = x^P_{k+1} + K_K (y^m_{k+1} - Cx^P_{k+1}) \quad (7)$$

$$P^F = P^P - K_K C P^P, \quad (8)$$

where P^P is the state covariance matrix in prediction stage. Eqs. (4-5) are concerned with the prediction stage that is separated from the correction stage, Eqs. (7-8), by the gain update given by Eq. (6). The optimal state estimation, based on the measured sequences, is represented by Eq. (7).

3. Kalman Filtering QR Tuning

Aiming to develop a procedure to support metaheuristics or Bayesian inference to guide the Q and R matrices selection of *Kalman* filter gain. The SKF basic equations, Eqs. (4)-(8), can be represented in terms of its parameters functionality to insert the duality principles in matrices selection procedure. The P^P state prediction covariance matrix, Eq. (4), is strongly related with the K_K gain and Q covariance,

$$P^P = f_1(P^F, A, B, Q) \quad (9)$$

The gain mapping,

$$K_K = f_2(P^P, C, R) \quad (10)$$

As can be evaluated by Eq. (10), the K_K *Kalman* gain is dependent only of three parameters, the P^P predicted state is a mapping of P^F , A , Q and B . If the P^P covariance matrix is replaced by its quadratic form, Eq. (4), in Eq. (6) a new mapping for K_K is given by

$$K_K = f_K(A, P^F, \Gamma, Q, C, R) \quad (11)$$

The observers gains, Eq. (11), are assembled to explicitly represent the relation between Q and R matrices. Considering $BQB^T \gg APA^T$ and $R \gg CPC^T$. If $C \equiv I$ and $B = I$, the $K_k \approx Q/R$ approximation for *Kalman's* gain is and its simplified mapping is given by,

$$K_K = f_K^{\text{approx}}(Q, R) \quad (12)$$

Relation (12) shows the strong influence of Q and R covariances matrices on the f_K^{approx} mapping for the gain adjustment, if certain restrictions are respected in system modeling design. The proposed procedure is the basic procedure chosen to guide the search, independently of the method to evaluate these matrices.

4. QR Duality Gains Design

In this section is presented the Q and R matrices general procedure to tune de *Kalman* filter gains. These matrices are implemented in the process computer to make the performance evaluation of the filter. The results are compared with other filters, such as $\alpha\beta\delta$ and polynomial type, with the purpose of evaluate the robustness of SKF in presence of operation changes.

4.1. Reduction Cell Modeling

The reduction cell modeling is performed in a third order state space description. Three states variables related with resistance of reduction cell dynamics are represented in state space description. Replacing the values of the dynamic system matrix A and output matrix C , in Eq. (1),

$$\dot{x} = \begin{bmatrix} 1.00 & 1.00 & 0.00 \\ 0.00 & 1.00 & 1.00 \\ 0.00 & 0.00 & 1.00 \end{bmatrix} \begin{bmatrix} x_k^R \\ x_k^{slope} \\ x_k^{curv} \end{bmatrix} + \zeta \quad (13)$$

$$y = \begin{bmatrix} 1.00 & 0.00 & 0.00 \end{bmatrix} \begin{bmatrix} x_k^R \\ x_k^{slope} \\ x_k^{curv} \end{bmatrix} + v ,$$

where $[x_k^R x_k^{slope} x_k^{curv}]$ are the state variables that represent the filtered resistance, the resistance and curvature, respectively. y_k represents the resistance calculated from the pot voltage and line current. The model eigenvalues are in the unit circle contour, the computed eigenvalues are 1, 1 and 1. The observability matrix rank is 3, this value guarantees the construction of the model states by pot the resistance measurements.

4.2. Voltage and Current Measurements

The measured values of pot voltage and line current, as well as the calculated resistance, are shown at a sampling time of 1 second. The filtered resistance and estimated slope and curvature behavior can be seen in Fig. 2.

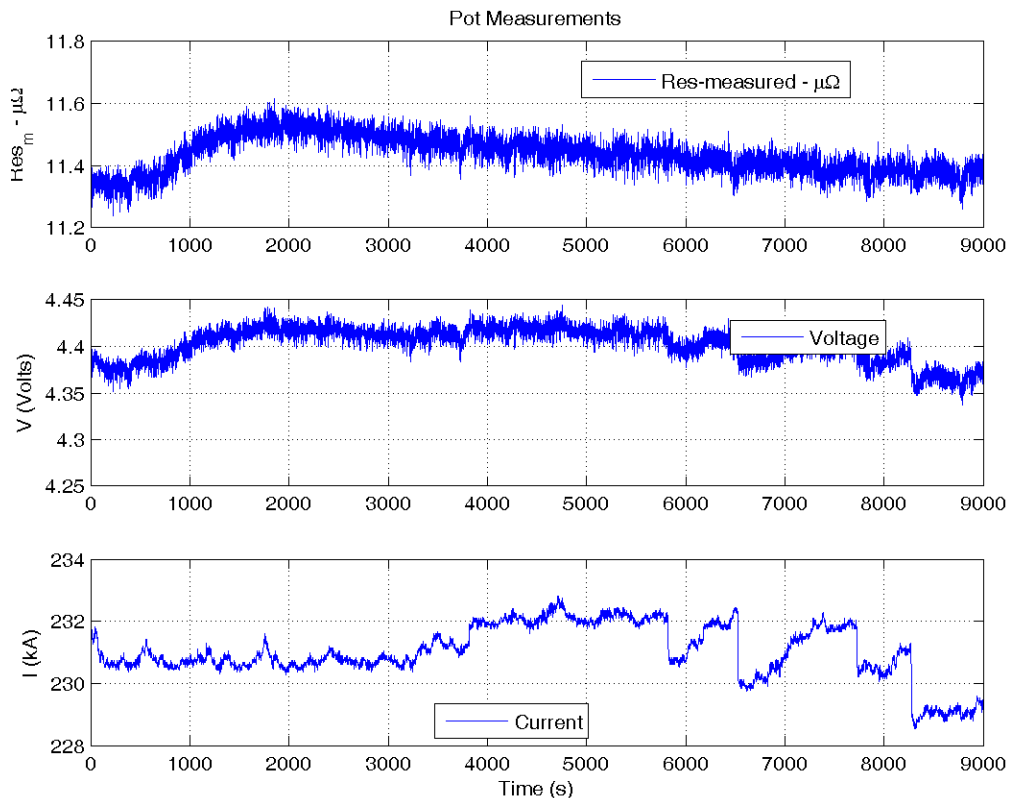


Fig. 2. Voltage, current and resistance measurements in the bath.

The reduction cell voltage and **line** current are represented as the reduction resistance to be used as the only measured state variable, equation (2), in section 2. This resistance is used as the measured output of the *Kalman* filter, equation (7), in section 2, to predict the reduction cell slope and curvature states.

A statistical analysis of the incoming inputs (voltage and current) and calculated resistance helps to understand the distribution of the values around the mean, and it is useful to understand the nature of the variations during the different stages of the normal operation.

The computed resistance and measured signals means, deviation, maximums and minimums, Table 1, and related with its time behavior. As can be observed, the pot is working under normal operational conditions.

Table 1. Resistance, Voltage and Current Statistics.

	Measurements		
	Resistance	Voltage	Current
	$\mu\Omega$	V	kA
Mean	11.4421	4.3687	227.991
Max	11.627	4.423	233.542
Min	11.159	4.273	220.677
Std	0.083	0.0248	1.279
Cov	0.007	0.0006	1.637

The pot operation mode, Fig. 3, and histograms, Fig. 4, reflects the resistance behaviour during different feed control.

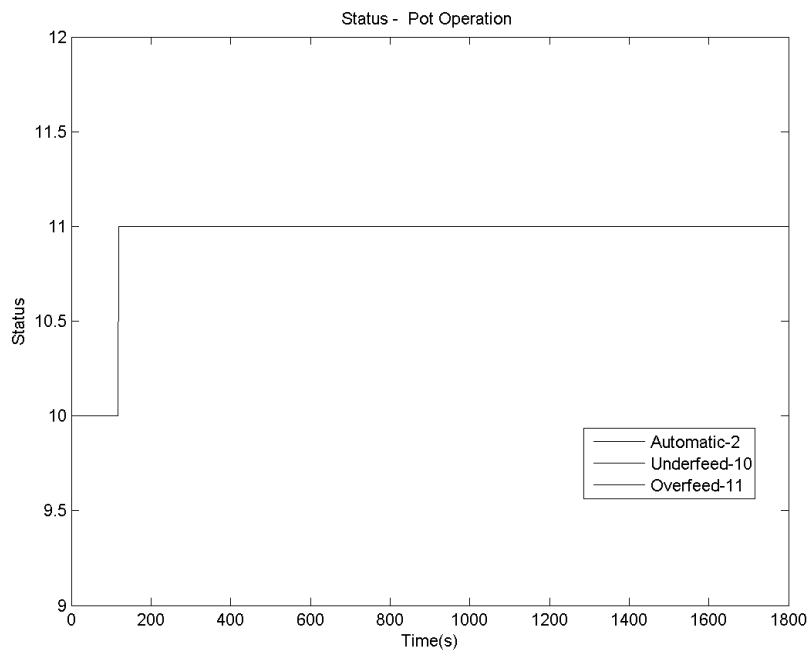


Fig. 3. Reduction Cell Status of Operation.

4.3. Gains Adjustment

A procedure to tune the *Kalman* filter gains is based on duality relation, equation (12), following the guidelines suggested by [2], and afterwards it is compared with other digital filter implementations. The variations matrices are associated with the bandwidth of *Kalman*'s filter and its stability. The procedure strategy is based on the functional mapping,

$$K_n = f(Q_n, R) \tag{14}$$

The values of R matrix are kept fixed for gains adjustment and variations are applied in covariances of matrix Q . The mapping of equation (14) for a sequence of five Q covariances deviations is presented in Table 2.

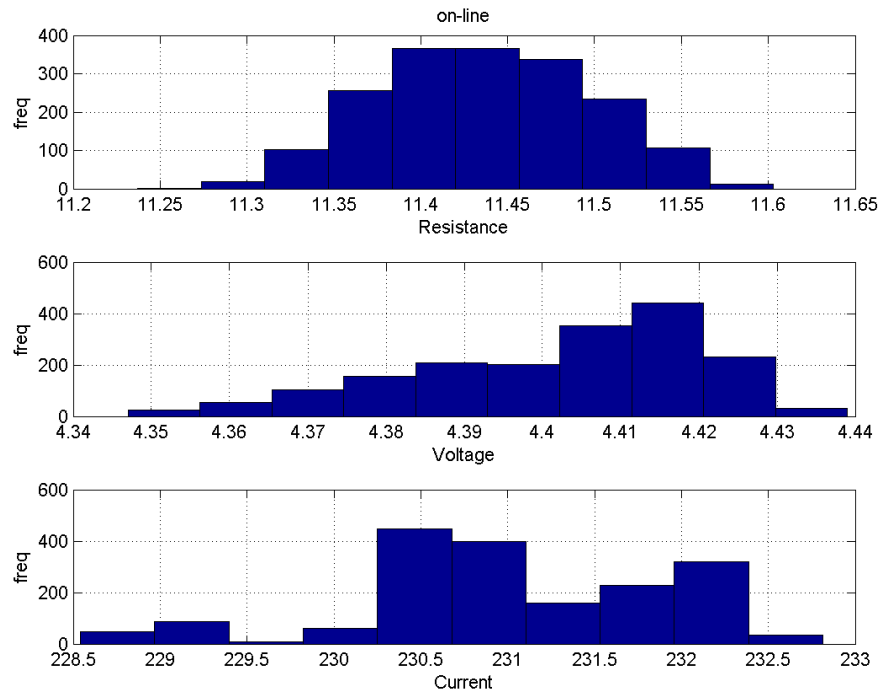


Fig. 4. Resistance, Voltage and Current.

Table 2. Covariance Matrices for Bandwidth Adjustment of Kalman Filter.

Q_n, R	Covariance			
	r_{11}	q_{11}	q_{22}	q_{33}
1	2.0×10^{-2}	1×10^{-6}	1×10^{-6}	1×10^{-6}
2	2.0×10^{-2}	1×10^{-7}	1×10^{-7}	1×10^{-7}
3	2.0×10^{-2}	1×10^{-9}	1×10^{-9}	1×10^{-9}
4	2.0×10^{-2}	1×10^{-14}	1×10^{-14}	1×10^{-14}
5	2.0×10^{-2}	1×10^{-16}	1×10^{-16}	1×10^{-16}
6	2.0×10^{-2}	1×10^{-18}	1×10^{-18}	1×10^{-1}
7	2.0×10^{-2}	1×10^{-18}	1×10^{-18}	1×10^{-20}
8	2.0×10^{-2}	1×10^{-18}	1×10^{-18}	1×10^{-30}
9	2.0×10^{-2}	1×10^{-18}	1×10^{-10}	1×10^{-30}
10	2.0×10^{-2}	1×10^{-10}	1×10^{-10}	1×10^{-30}
11	2.0×10^{-2}	1×10^{-6}	1×10^{-10}	1×10^{-15}
12	2.0×10^{-2}	1×10^{-1}	1×10^{-10}	1×10^{-20}

The covariances matrices variations and theirs associated gains are shown in Tables 2 and 3,

respectively. The filter's gains are evaluated considering a mapping $f(Q; R) \rightarrow K_k$, the stochastic matrices spaces $Q_{3 \times 3}$ and $R_{1 \times 1}$ are mapped into K_3 Kalman gain.

Table 3. Kalman Filter Gains.

K_n	GAINS		
	K_1	K_2	K_3
1	7.9390×10^{-2}	3.3170×10^{-3}	6.7846×10^{-5}
2	5.4792×10^{-2}	1.5545×10^{-3}	2.1739×10^{-5}
3	2.5815×10^{-2}	3.3867×10^{-4}	2.2070×10^{-6}
4	3.8314×10^{-3}	7.3575×10^{-6}	7.0575×10^{-9}
5	1.7835×10^{-3}	1.5906×10^{-6}	7.0756×10^{-10}
6	1.0302×10^{-3}	4.8365×10^{-7}	1.0014×10^{-10}
7	9.9985×10^{-4}	4.4470×10^{-7}	8.2456×10^{-11}
8	9.9953×10^{-4}	4.4429×10^{-7}	8.2272×10^{-11}
9	1.3716×10^{-3}	9.2155×10^{-7}	1.2745×10^{-10}
10	1.3716×10^{-3}	9.2155×10^{-7}	1.2745×10^{-10}
11	2.6494×10^{-3}	3.5128×10^{-6}	2.2332×10^{-9}
12	2.2552×10^{-2}	1.0026×10^{-5}	1.6729×10^{-9}

The SKF bandwidth variations and the time response are analyzed for the five Kalman gains adjustments are presented in Table 3 and are associated with Figs. 5, 6 and 7.

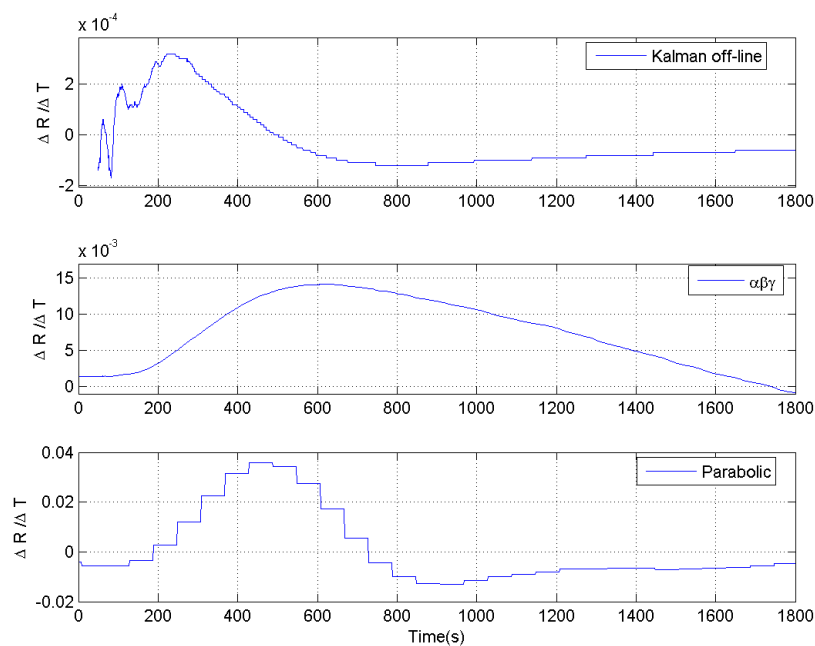


Fig. 5. Case 12 - Estimated Slope of the Reduction Cell.

Observing Figs. 5 and 6, we note that bandwidth is reduced as the Q matrix has its eigenvalues tending to zero, Table 2. Consequently, provokes the attenuation of the high frequencies behaviors. Comparing the SKF filter estimation with the parabolic filter in Figs. 5 and 6, we observe that SKF is able to reproduce. The same behavior of the comparison filters by the adjustment of matrices Q and R.

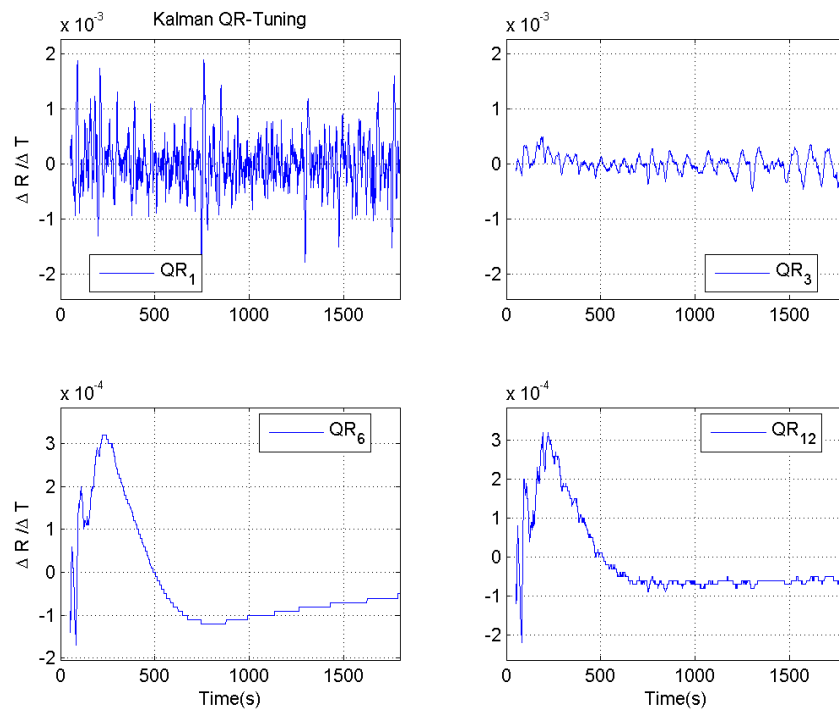


Fig. 6. Reduction Cell Estimated Slope for QR-Tuning.

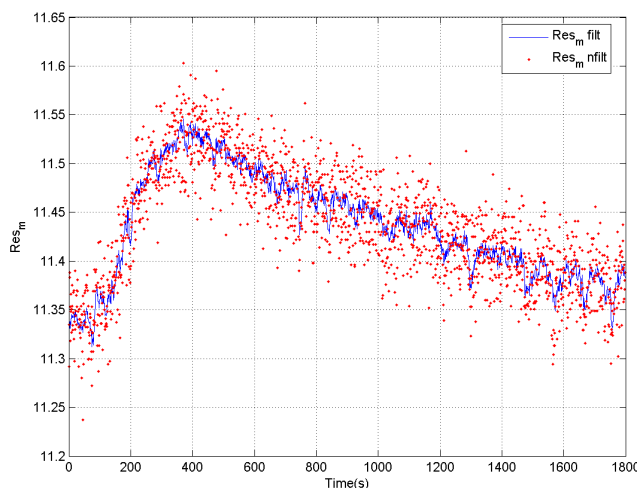


Fig. 7. Measured and Estimated Resistance.

The chosen heuristic to apply the QR duality principle is based on the relation. The R variance matrix is fixed in a value that is greater than Q values. Observing Figs. 5 and 6, it is verified that the gains adjusted by QR duality principle, Table 3, impose a band of operation in standard Kalman filter. This operation goes from a low to high bandpass operation.

A functional pattern for the gain adjustment can be proposed based on the statistics of the measurements. It is observed that Q matrix decreasing imposes a gain decreasing that has a $K_k \approx Q/R$ relation from 10^{-2} to 10^{-8} for the first Q and R variations of Table 2. Cases 3 and 4 had shown bandwidth enlargement as Q matrix coefficients had decreased.

Consequently, if the Q diagonal variance matrix has its coefficients reduced, it means that the gain is reduced too. We can establish that if the gains are reduced the SKF works as a low bandpass filter. If its

gains are increased, the filter works as high bandpass filter. As can be seen in Fig. 6, the *Kalman* filter gains are designed to follow certain patterns that are imposed by the variation in the *Q* matrix.

5. SKF Real Time Performance

In this section, the indirect measurement system device is evaluated for on-line implementations. The results and practical aspects are discussed in context of hardware-software devices to evaluate the Al_2O_3 concentration in the electrolytic bath. The main goal is to evaluate the *Kalman* filter tuning algorithm based on the QR duality of its gains.

5.1. On line Estimation

The on-line filtering of resistance by the *Kalman* filter is presented in Fig. 7 and it is associated operational condition state estimation is shown in Fig. 3. This figure is used as reference for gains adjustment, in this manner, the *Q* and *R* matrices elements deviations effects are observed in the filtered resistance and non realist matrices are discarded as solutions.

5.2. Comparison

The on-line results estimated slope by *Kalman* filter, Fig. 8, is compared with the $\alpha\beta\gamma$ and parabolic filters. The main purpose is to evaluate the effectiveness of the proposed adjustment as a pattern tracking by QR duality gains adjustments.

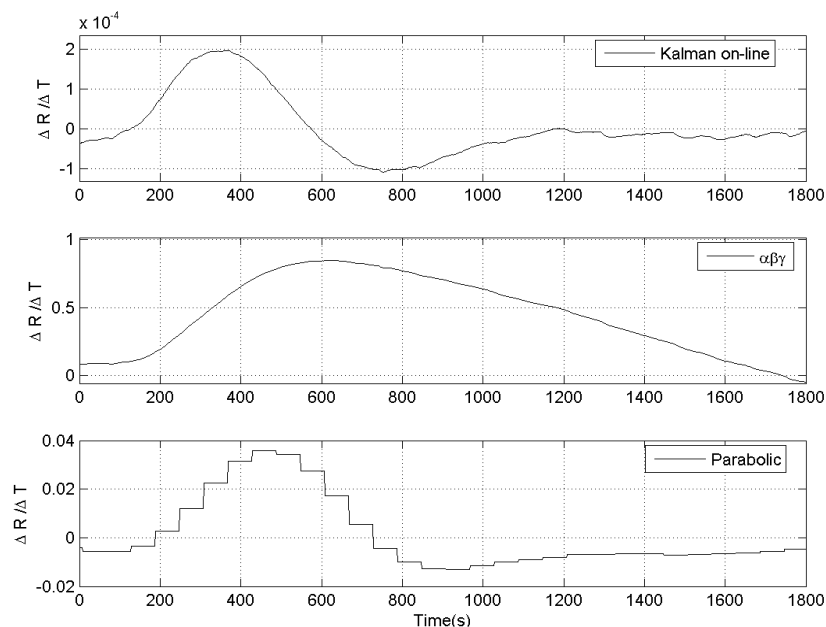


Fig. 8. Real Time Slopes of *Kalman*, $\alpha\beta\gamma$ and Parabolic Filters.

The first association of Figs. 3 and 8, the *Kalman* filter has a sensitivity for alumina concentration variation by the reduction cell resistance deviations, as can be seen in overfeed transition to under-feed phase. As a second association in Fig. 7 as the level of noise that is not filtered out depends on *Q* matrix selection.

6. Concluding Remarks

In this article it was presented a *Kalman* filtering bandwidth tuning procedure, based on *QR* matrices duality principle, for indirect measurement of Al_2O_3 concentration in the electrolytic bath. Specifically, the main goal was the indirect measurement of the Al_2O_3 concentration in reduction cell by deviations on the reduction cell resistance.

This research results had been applied to a real reduction cells. It focuses the use of the *QR* duality principle as a design framework for *Kalman* filter gain adjustment. The framework succeeds in the determination of trial and error heuristic. The improvement of the framework performance can be done by the inclusion of genetic algorithms for the *Q* and *R* searches and a Bayesian inference engine. Likewise, the development of neural networks to solve the algebraic *Riccati* equation for multivariable stochastic state space observers, as an alternative way to by pass the inverse problem computation due to multiple outputs. Also, a metaheuristic and evolutionary algorithms can be s consider to help the tuning of the *Kalman* filter gains.

The proposed method had proven to be good alternative to make the gain adjustment of *Kalman* when it is used for the indirect measurement of Al_2O_3 concentration. Especially good is its flexibility on patterns tracking, based on the covariances matrices estimation for the bandwidth adjustment and to improve transient response. In addition to this, the robustness of the filter had been kept along various stages of the normal pot operation, in counterpoint to others filtering methods that have been used widely in the aluminium industry.

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